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Abstract: Write paper abstract here, less than 200 words. Font size 10, except for the reference which is font size 8. Do not use page number.

Introduction: Give background introduction and any technical information for the work described here.

Design and Implementation: Give detailed design and implementation or software work here. The section title can be altered to suit the content written.

Results and Discussion: Give a good analyses and discussion for the results obtained.

Conclusion: Provide a short conclusion for the paper.

References

[1] C. Liu et al., *IEEE Electron Device Letters*, vol. 36, pp. 38, 2015.
[2] H. Huang, et al., *IEEE Trans. On Power Electronics,* Vol.35, pp. 59, 2018.
[3] Y-H, Wang, et al., *IEEE Electron Device Lett*. Vol. 36, pp. 38, 2019.
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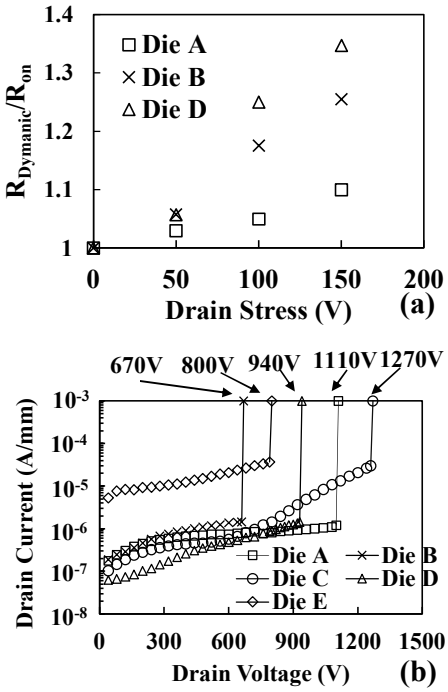


Fig. 1 (a) The ratio between the dynamic on-resistance ($R_{Dynamic}$) and the static on-resistance (R_{on}) of Dies A, B and D after drain stress at 10V for 10s. Ar treatment is found to have suppressed the current collapse effect of the ICP-fluorinated device (Die B) by about 10%. **(b)** I_D-V_D performance of Dies A~E under the off-state at V_G = 0V for all dies except for Die A at V_G = −5V. Ar pre-fluorination treatment is able to enhance the breakdown voltage (BV) from 670V to 1270V without sacrificing the on-state conductivity, making their BV comparable to un-fluorinated Die A.